

**Amendment to the Title**

Please replace the title with the following new title:

**METHOD OF FORMING TRENCH IN SEMICONDUCTOR DEVICE USING POLISH  
STOP LAYER AND ANTI-REFLECTION COATING**

**Amendment to the Specification**

Page 1, line 1, please replace the title paragraph beginning "METHOD OF FORMING"  
with the following new title paragraph:

**METHOD OF FORMING TRENCH IN SEMICONDUCTOR DEVICE USING POLISH  
STOP LAYER AND ANTI-REFLECTION COATING**

Page 4, please replace paragraph [0015] with the following:

[0015] ~~Prior to~~ After forming a polish stop layer on a semiconductor substrate, an antireflection coating is formed on the polish stop layer, and the anti-reflection coating is selectively etched to form an anti-reflection coating pattern. An area of the polish stop layer exposed through the anti-reflection coating pattern and the semiconductor substrate to a predetermined depth are etched to form the trench, and ends of the anti-reflection coating pattern and ends of the polish stop layer under the ends of the antireflection coating pattern are etched such that the ends of the anti-reflection coating are formed into a rounded configuration.